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Supporting Information

Enhancement of Electrical Performance of Atomic Layer Deposited SnO Films via Substrate Surface Engineering

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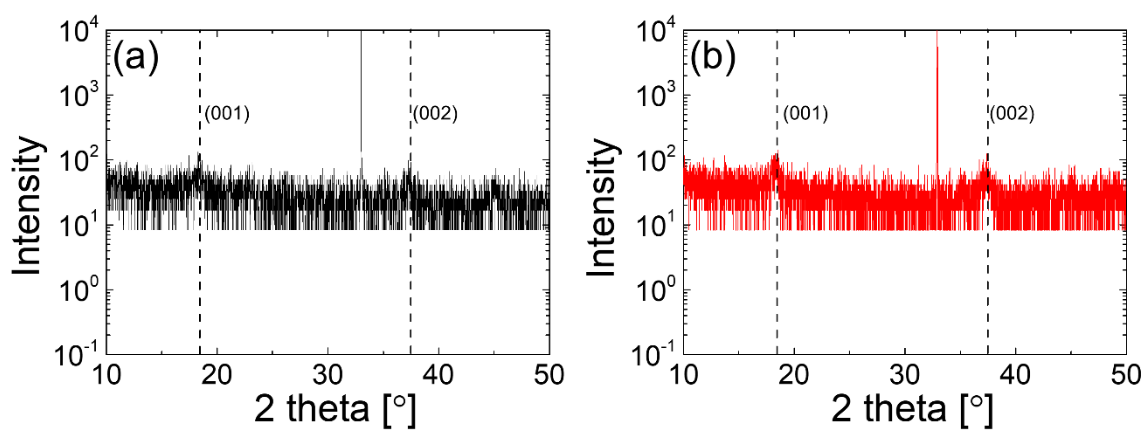

Figure S1. XRD patterns of the SnO films deposited on (a) the as-cleaned SiO_2 and (b) the plasma-treated SiO_2.

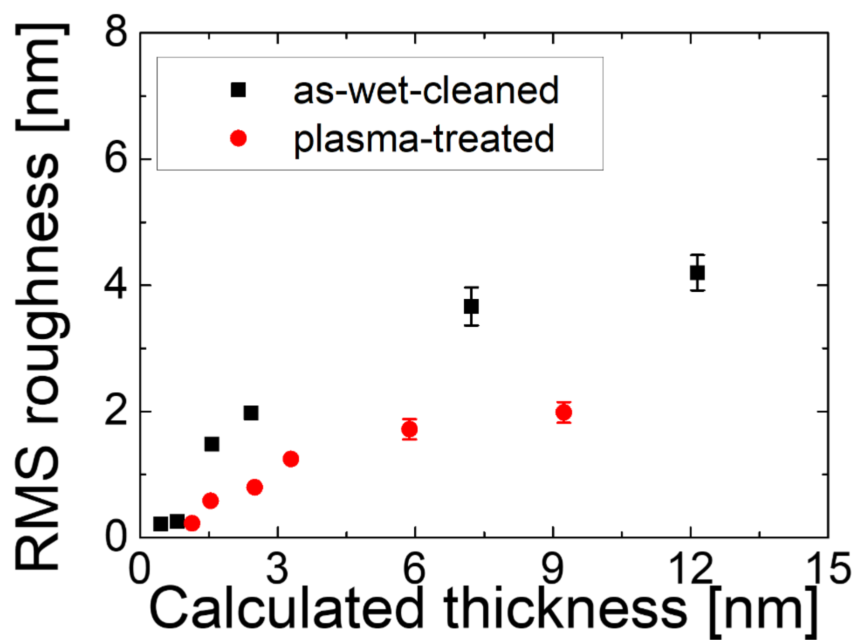

Figure S2. Variation in the RMS roughness of the SnO films grown on the as-wet-cleaned and plasma-treated SiO_2 substrates as a function of the film thickness.

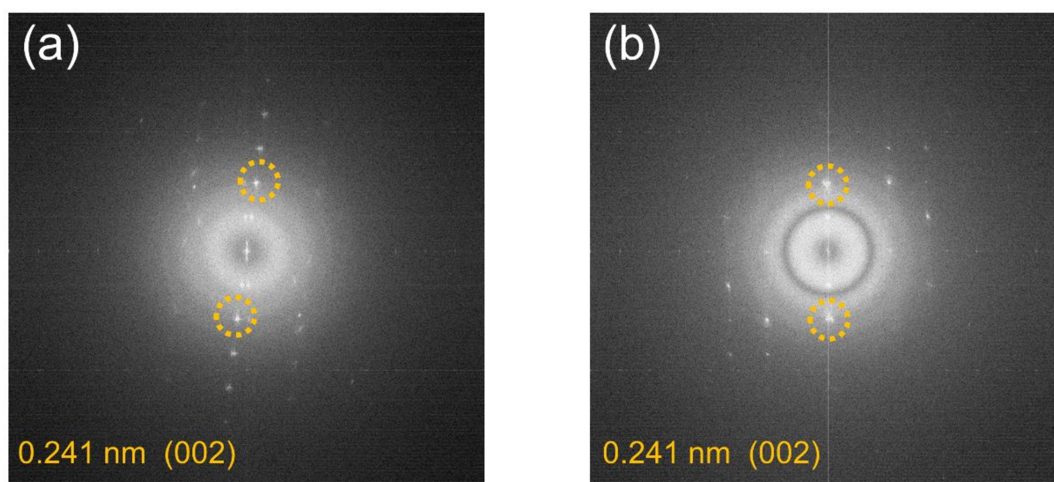

Figure S3. The fast Fourier transform images corresponding to the HRTEM images in (a) Fig. 4(a) and (b) Fig. 4(b).

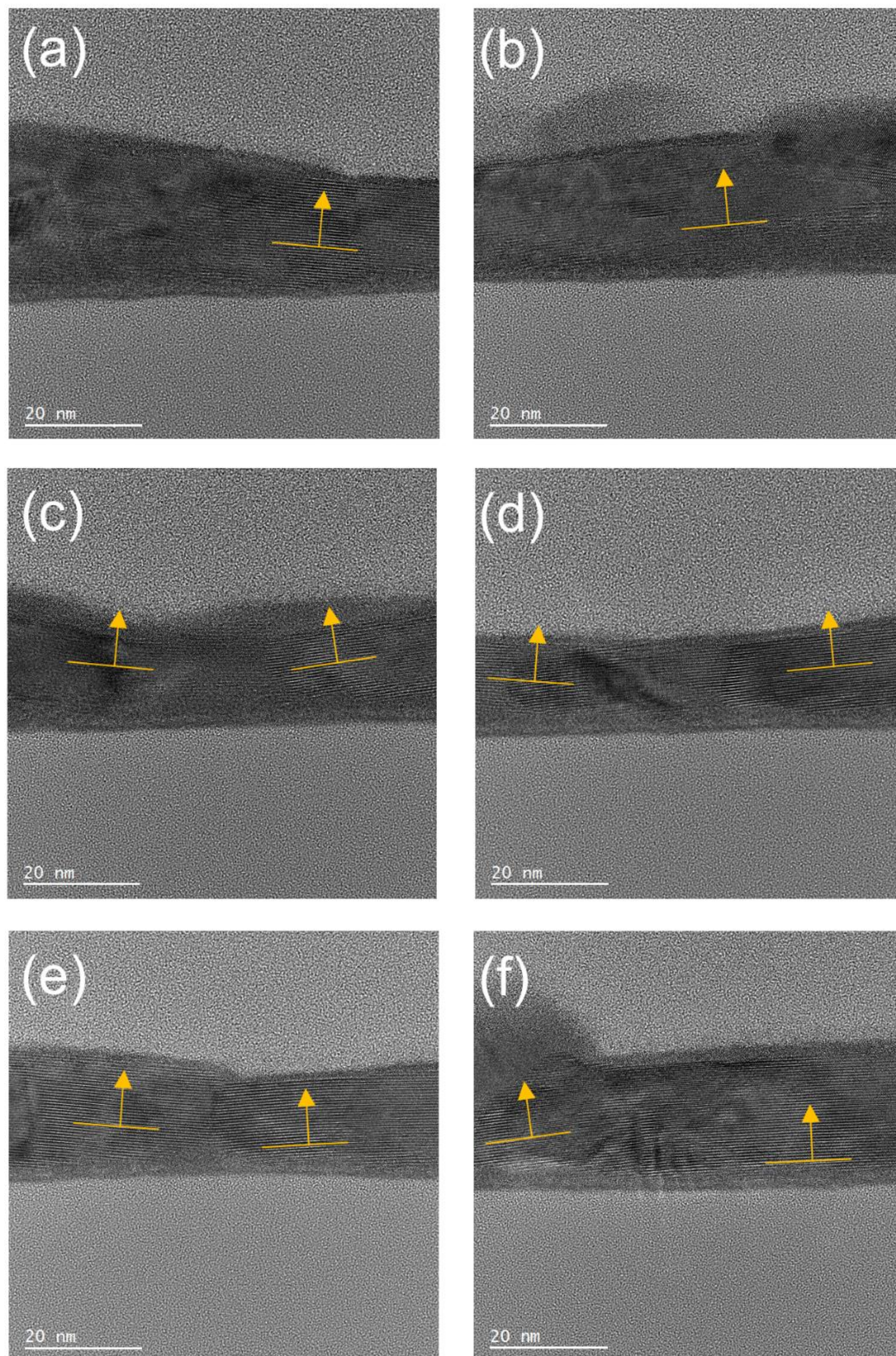

Figure S4. (a)-(f) HRTEM images obtained from multiple regions in the SnO film grown on the as-cleaned SiO_2.

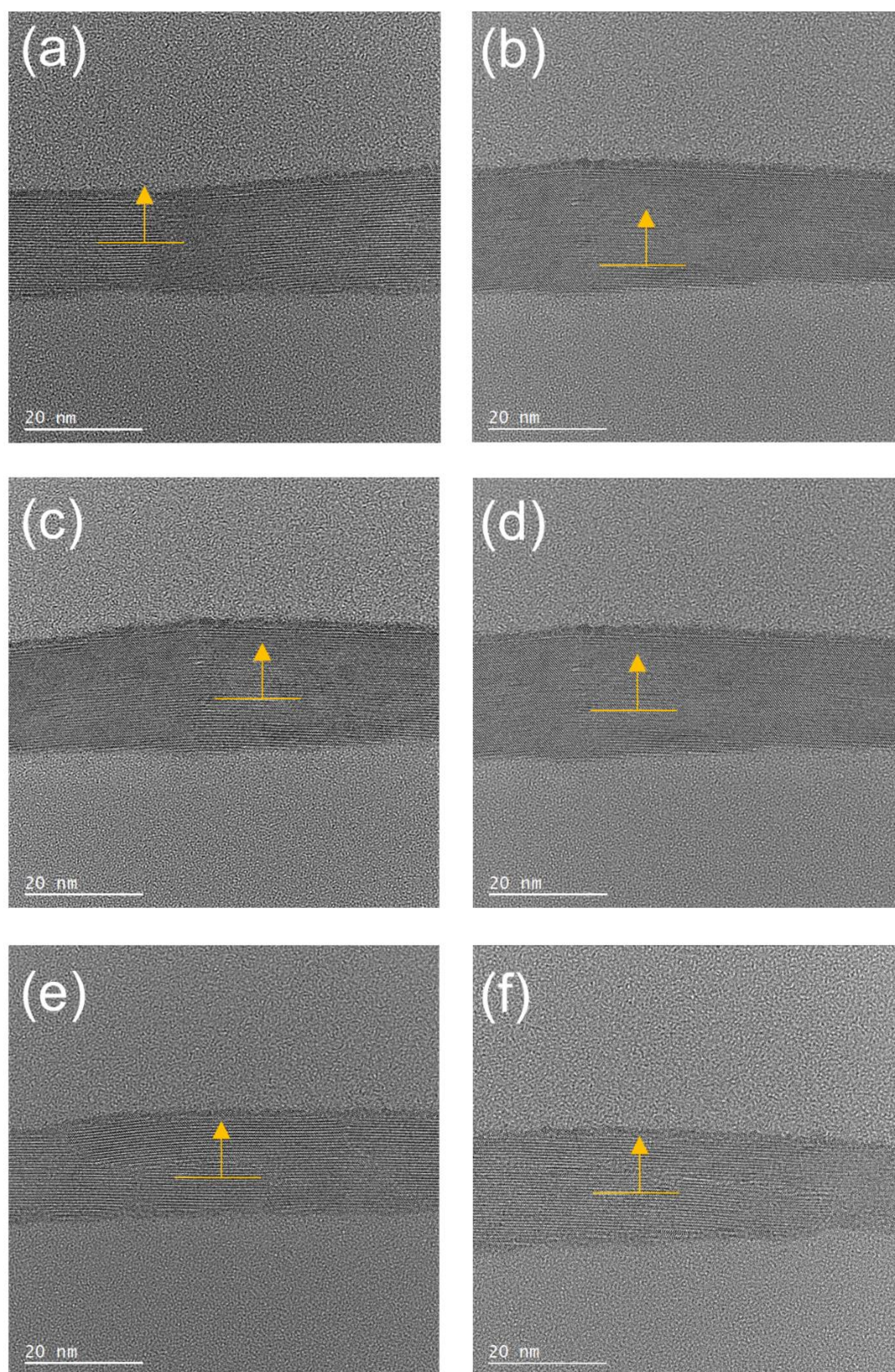

Figure S5. (a)-(f) HRTEM images obtained from multiple regions in the SnO film grown on the plasma-treated SiO_2.

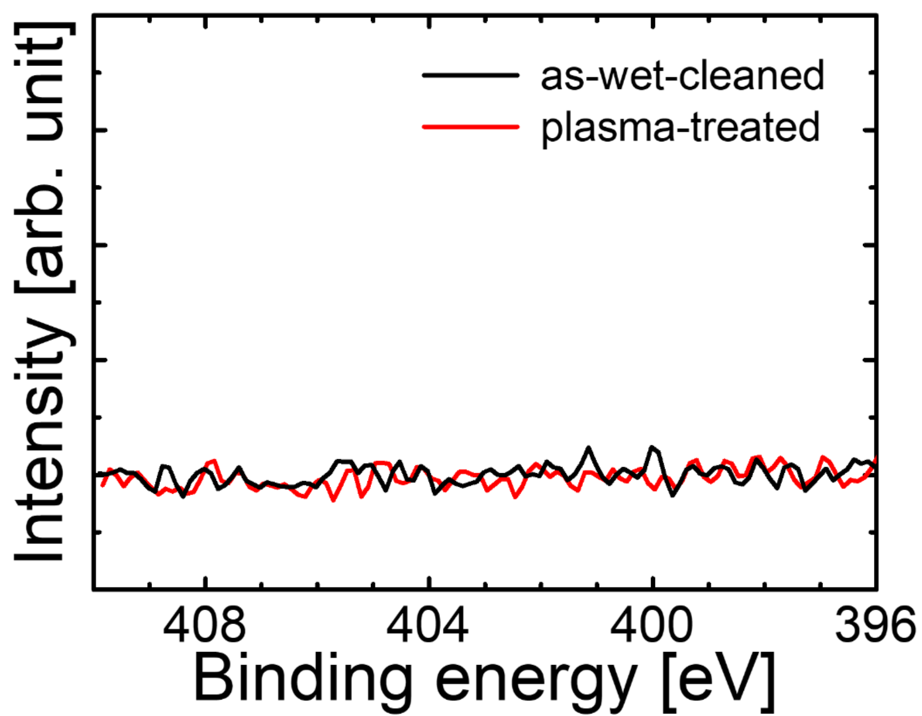

Figure S6. XPS spectra of N 1s core level of the as-wet-cleaned, and plasma-treated SiO_2.

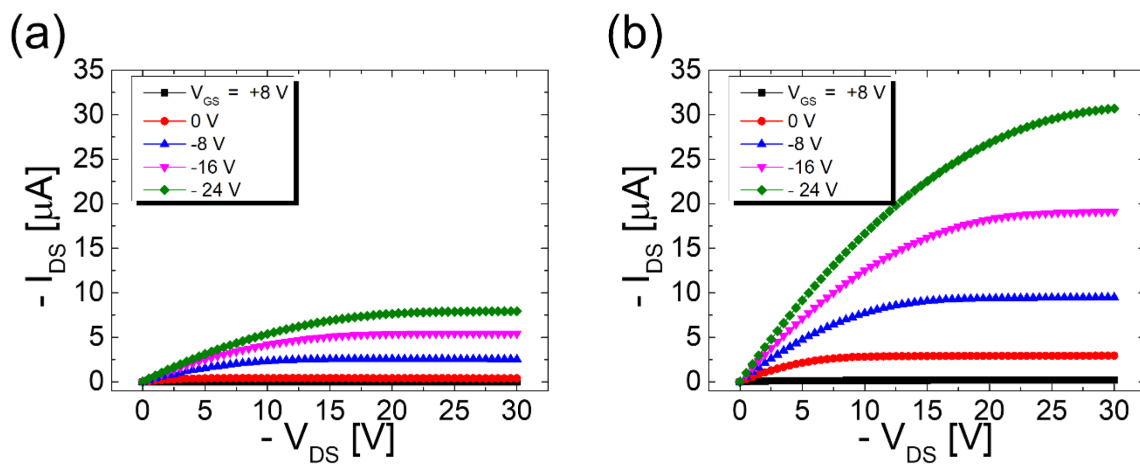

Figure S7. Output curves of the bottom gate-structured TFTs fabricated with the SnO grown on (a) the as-wet-cleaned SiO_2 and (b) plasma-treated SiO_2.